

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

US3A THRU US3M

SURFACE MOUNT ULTRA FAST SWITCHING RECTIFIER

TECHNICAL SPECIFICATION

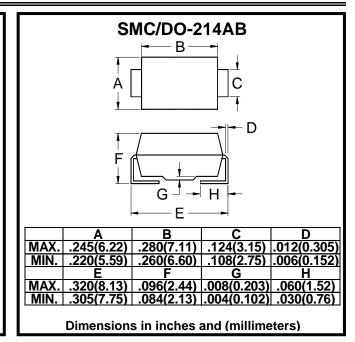
VOLTAGE: 50 TO 1000V CURRENT: 3.0A

FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Ultra fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	US 3A	US 3B	US 3D	US 3G	US 3J	US 3K	US 3M	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current (T _L =75°C)	I _{F(AV)}	3.0							Α
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	100						А	
Maximum Instantaneous Forward Voltage (at rated forward current)	V_{F}	1.0 1.4					1.7		V
Maximum DC Reverse Current $T_a=25^{\circ}$ C (at rated DC blocking voltage) $T_a=100^{\circ}$ C		10.0 500					μ Α μ Α		
Maximum Reverse Recovery Time (Note 1)	trr	50				75			nS
Typical Junction Capacitance (Note 2)	C_{J}	45						pF	
Typical Thermal Resistance (Note 3)	R _θ (ja)	25						°C/W	
Storage and Operation Junction Temperature	T_{STG},T_{J}	-50 to +150						°C	

Note:

- 1.Reverse recovery condition I_F=0.5A, I_R=1.0A,Irr=0.25A.
- 2.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
- 3. Thermal resistance from junction to terminal mounted on 5x5mm copper pad area

http://www.sse-diode.com